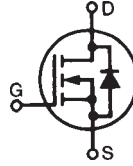


Polar™ Power MOSFET

IXTA08N100P
IXTP08N100P
IXTY08N100P

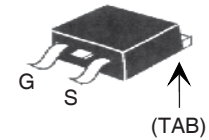
$V_{DSS} = 1000V$
 $I_{D25} = 0.8A$
 $R_{DS(on)} \leq 20\Omega$

N-Channel Enhancement Mode
Avalanche Rated

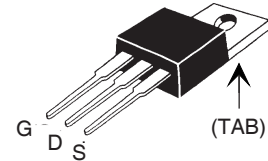


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	1000	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	1000	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ C$	0.8	A
I_{DM}	$T_C = 25^\circ C$, pulse width limited by T_{JM}	1.5	A
I_A	$T_C = 25^\circ C$	0.8	A
E_{AS}	$T_C = 25^\circ C$	80	mJ
dV/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	10	V/ns
P_D	$T_C = 25^\circ C$	42	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062) from case for 10s	300	$^\circ C$
T_{SOLD}	Plastic body for 10s	260	$^\circ C$
M_d	Mounting torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-263	2.50	g
	TO-220	3.00	g
	TO-252	0.35	g

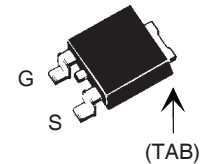
TO-263 (IXTA)



TO-220 (IXTP)



TO-252 (IXTY)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

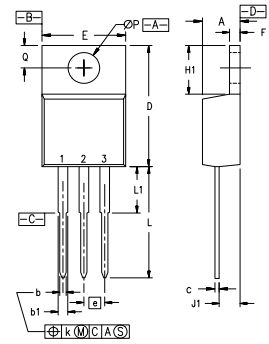
Applications

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor controls
- Robotics and servo controls

Symbol	Test Conditions ($T_J = 25^\circ C$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 50\mu A$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 50 nA
I_{DSS}	$V_{DS} = V_{DSS}$			3 μA
	$V_{GS} = 0V$ $T_J = 125^\circ C$			100 μA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1	17	20	Ω

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 30\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	0.35	0.60	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		240	pF
			18	pF
			3.6	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 50\Omega$ (External)		20	ns
			26	ns
			55	ns
			24	ns
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		11.3	nC
			1.7	nC
			6.7	nC
R_{thJC} R_{thCS}	(TO-220)	0.50	3.0	$^\circ\text{C/W}$ $^\circ\text{C/W}$

TO-220 (IXTP) Outline



Pins: 1 - Gate 2 - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Source-Drain Diode

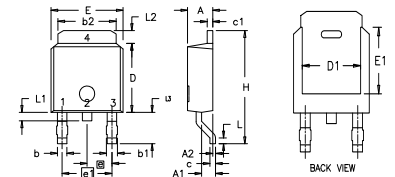
Characteristic Values

($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			0.8 A
I_{SM}	Repetitive, pulse width limited by T_{JM}			2.4 A
V_{SD}	$I_F = I_s$, $V_{GS} = 0\text{V}$, Note 1			1.5 V
t_{rr}	$I_F = 0.8\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$, $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		750	ns

Note 1: Pulse test, $t \leq 300 \mu\text{s}$; duty cycle, $d \leq 2\%$.

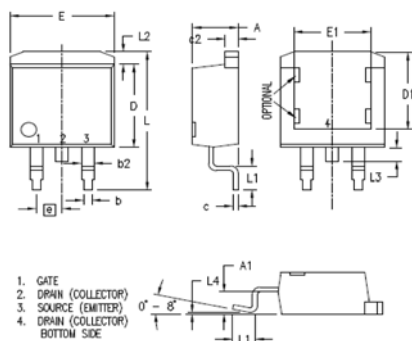
TO-252 (IXTY) Outline



Pins: 1 - Gate 2,4 - Drain
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
e1	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

TO-263 (IXTA) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b1	.045	.055	1.14	1.40
b2	.016	.029	0.40	0.74
c	.046	.058	1.14	1.40
c1	.046	.058	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

Fig. 1. Output Characteristics @ 25°C

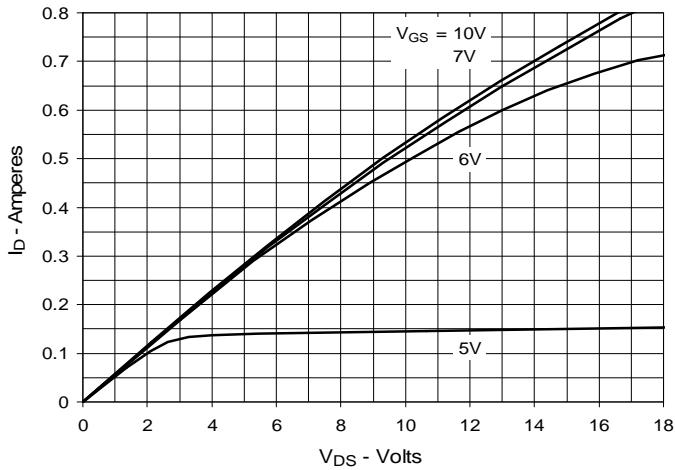


Fig. 2. Extended Output Characteristics @ 25°C

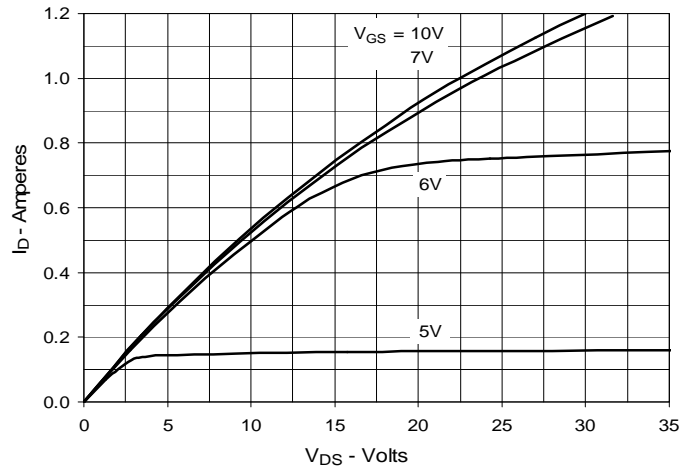


Fig. 3. Output Characteristics @ 125°C

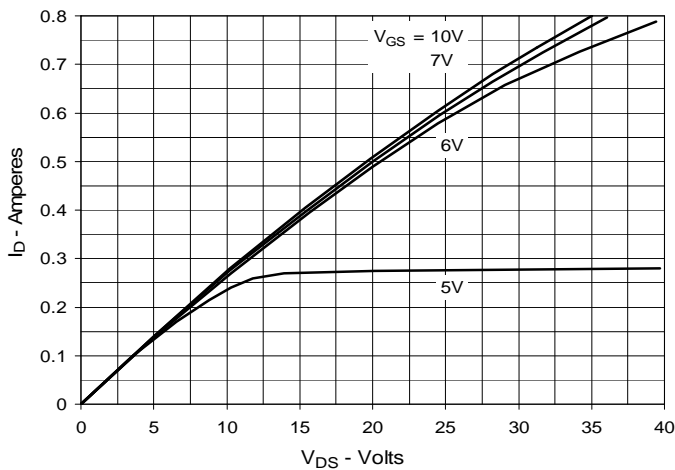


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 0.4A$ Value vs. Junction Temperature

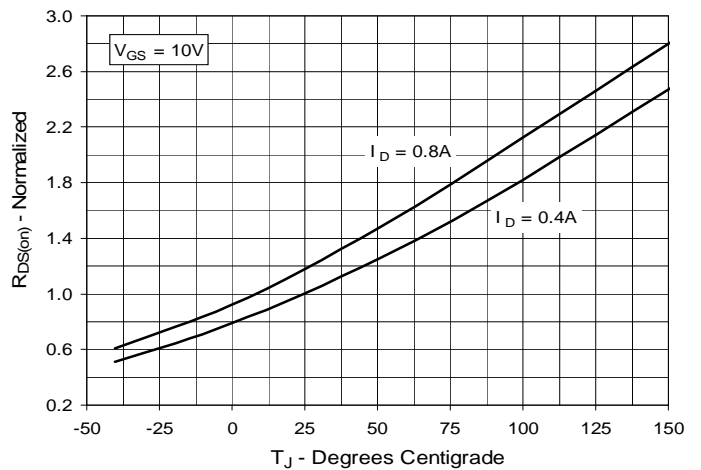


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 0.4A$ Value vs. Drain Current

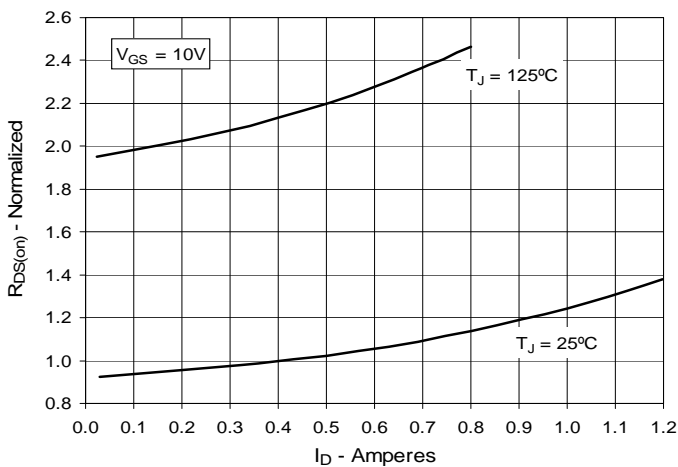


Fig. 6. Maximum Drain Current vs. Case Temperature

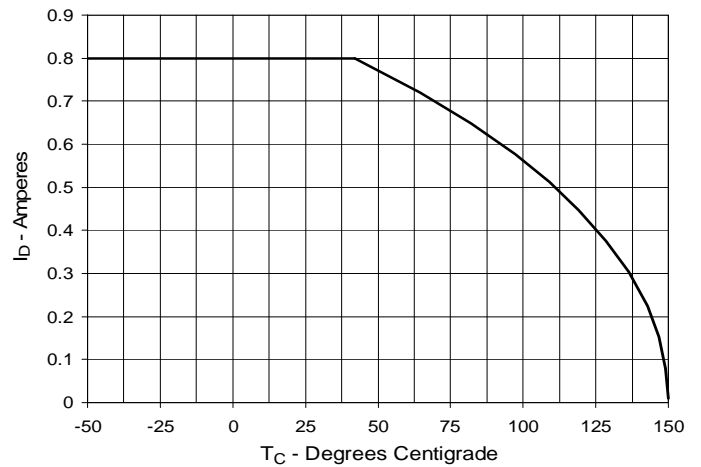


Fig. 7. Input Admittance

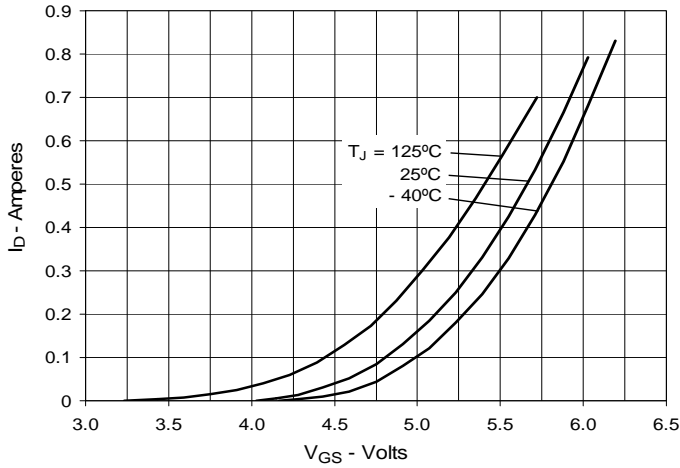


Fig. 8. Transconductance

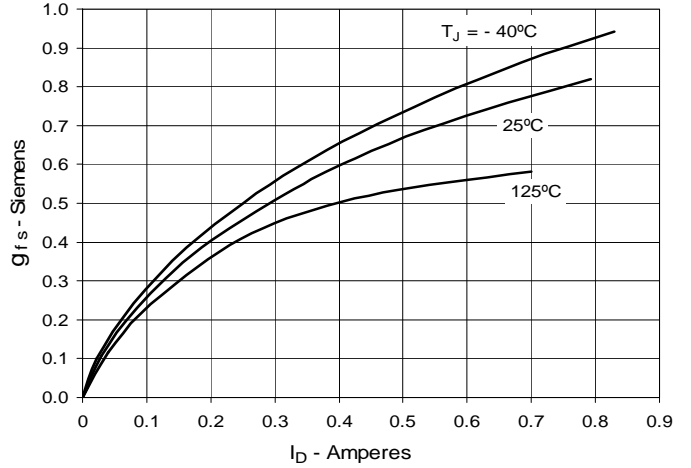


Fig. 9. Forward Voltage Drop of Intrinsic Diode

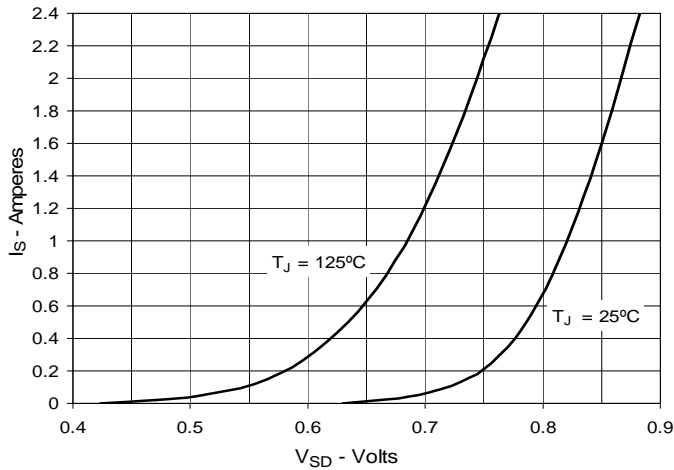


Fig. 10. Gate Charge

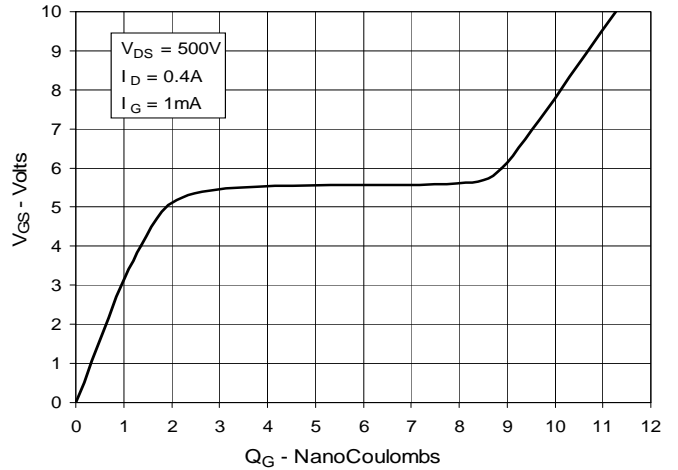


Fig. 11. Capacitance

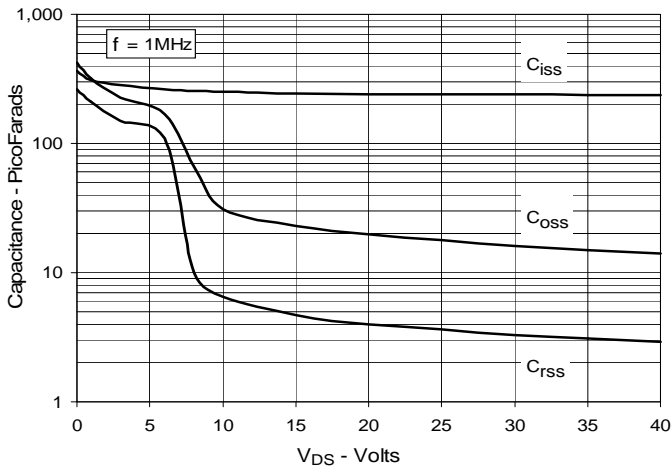


Fig. 12. Maximum Transient Thermal Impedance

